Power Inductor HPC4018B-4R7M

ECN HISTORY LIST

REV	DATE	DESCRIPTION	APPROVED	CHECKED	DRAWN
1.0	14/06/25	新 發 行	楊祥忠	詹偉特	徐允珮
備註					

Power Inductor

HPC4018B-4R7M

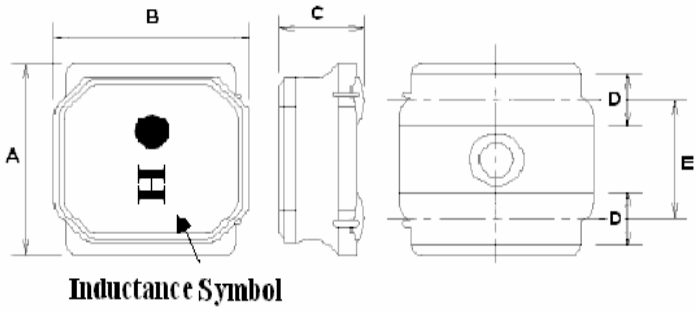
1. Features

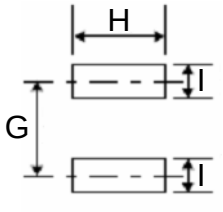
1. This specification applies Low Profile Power Inductors.
2. 100% Lead(Pb) & Halogen-Free and RoHS compliant.

Halogen-free

Pb-free

2. Dimension





Series	A(mm)	B(mm)	C(mm)	D(mm)	E(mm)	G(mm)	H(mm)	I(mm)
HPC4018B	4.0±0.2	4.0±0.2	1.8 max.	1.1±0.2	2.5±0.2	2.8 ref.	3.7 ref.	1.2 ref.

Units: mm

3. Part Numbering

HPC	4018	B	-	4R7	M
A	B	C		D	E

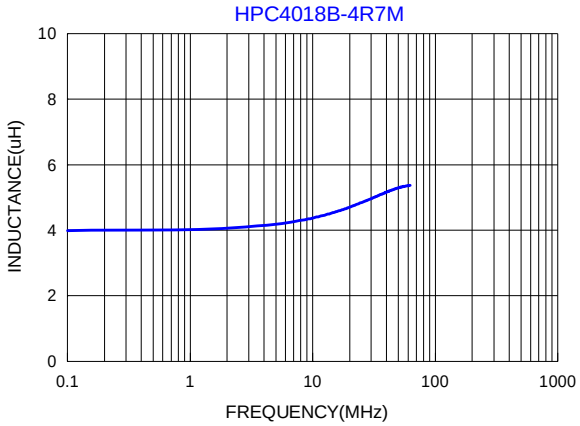
A: Series
B: Dimension
C: Control S/N
D: Inductance 4R7=4.7 uH
E: Inductance Tolerance M=±20%

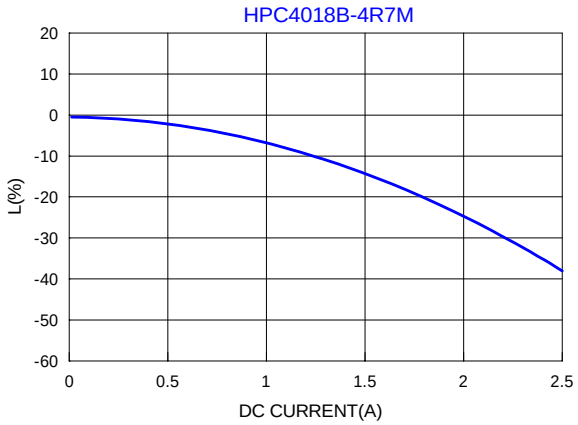
4. Specification

TAI-TECH Part Number	Inductance Symbol	Inductance (uH)	Tolerance (%)	Test Frequency (Hz)	SRF (MHz) min.	DCR (Ω) ±20%	I sat (A)	I rms (A)
HPC4018B-4R7M	H	4.7	±20%	1V100K	35	0.070	2.00	1.70

Note:

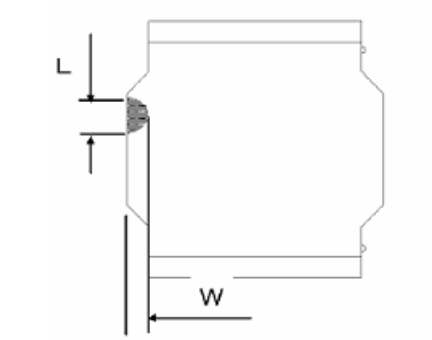
Isat：Based on inductance change （△L/L0：≦-30%）@ ambient temp. 25℃





Core chipping

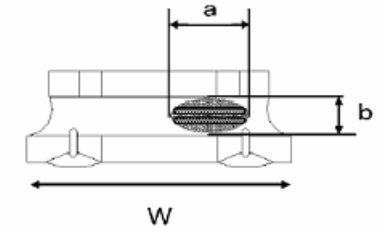
The appearance standard of the chipping size on top side, and bottom side ferrite core is listed below.



Type	L	W
HPC4018B	1.5mm Max.	1.5mm Max.

Void appearance tolerance Limit

Size of voids occurring to coating resin is specified below.



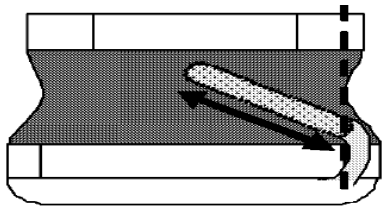
Exposed wire tolerance limit of coating resin part on product side.

Size of exposed wire occurring to coating resin is specified below.

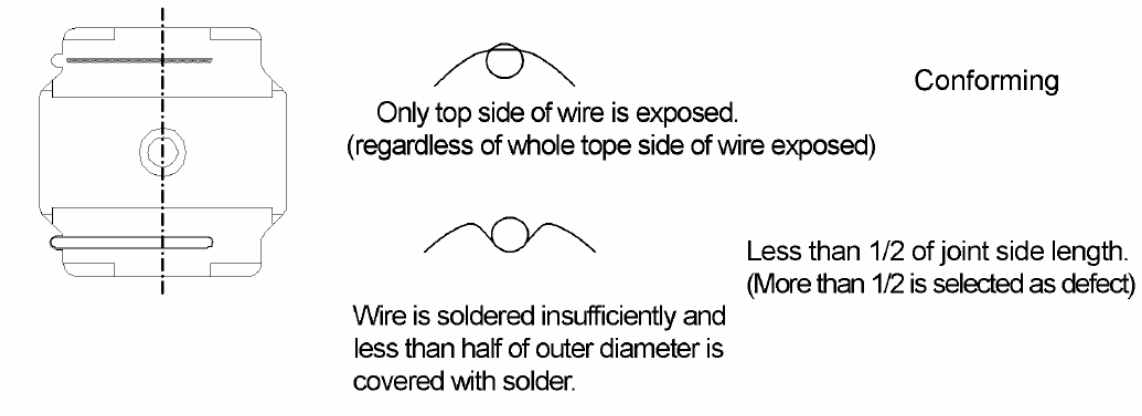
1. Width direction（dimension a）: Acceptable when a≦w/2
   Nonconforming when a＞w/2
2. Length direction（dimension b）: Dimension b is not specified.
3. The total area of exposed wire occurring to each sides is not greater than 50% of coating resin area, and is acceptable.

External appearance criterion for exposed wire

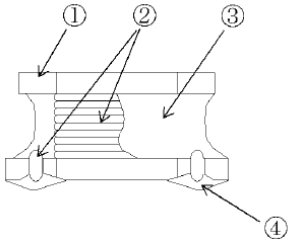
Exposed end of the winding wire at the secondary side should be 2mm and below.



5. Exectrde appearance criterion for exposed wire



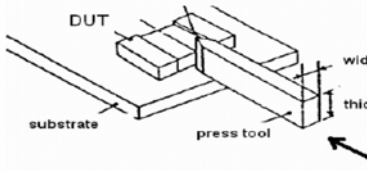
6. Material List



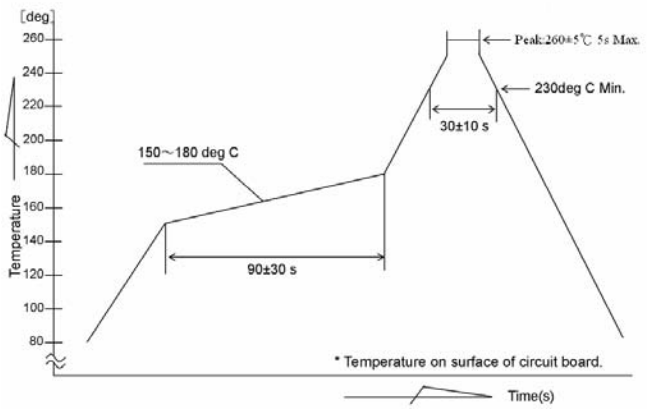
No.	Item	Material
1	Core	Ni-Zn ferrite
2	Wire	Copper Wire
3	Coating	Epoxy with magnetic
4	Solder	Lead free

7. Reliability and Test Condition

Item	Performance	Test Method and Remarks
Operating Temperature	-40~+85℃	Including self-generated heat
Storage Temperature	-40~+85℃(on board)	
Rated current	Within the specified tolerance	
Inductance (L)		LCR Meter: HP 4285A or equivalent, 100kHz, 1V
DC Resistance		DC Ohmmeter: HIOKI3227 or equivalent
Life Test	Appearance：No damage. Inductance：within±10% of initial value Q：Shall not exceed the specification value. RDC：within ±15% of initial value and shall not exceed the specification value	Preconditioning:Run through IR reflow for 2 times.(IPC/JEDEC J-STD-020DClassification Reflow Profiles) Temperature：125±2℃(Bead) Temperature： 85±2℃(Inductor) Applied current：rated current Duration：1000±12hrs Measured at room temperature after placing for 24±2 hrs
Load Humidity		Preconditioning:Run through IR reflow for 2 times.(IPC/JEDEC J-STD-020DClassification Reflow Profiles Humidity：85±2％R.H, Temperature：85℃±2℃ Duration：1000hrs Min. with 100% rated current Measured at room temperature after placing for 24±2 hrs
Thermal shock		Preconditioning:Run through IR reflow for 2 times.(IPC/JEDEC J-STD-020DClassification Reflow Profiles Condition for 1 cycle Step1：-40±2℃ 30±5min Step2：25±2℃ ≦0.5min Step3：105±2℃ 30±5min Number of cycles： 500 Measured at room fempraturc after placing for 24±2 hrs
Vibration		Oscillation Frequency: 10～2K～10Hz for 20 minutes Equipment： Vibration checker Total Amplitude:1.52mm±10% Testing Time : 12 hours(20 minutes, 12 cycles each of 3 orientations)。
Shock		<table><tr><td>Type</td><td>Peak value (g's)</td><td>Normal duration (D) (ms)</td><td>Wave form</td><td>Velocity change (Vi)ft/sec</td></tr><tr><td>SMD</td><td>1500</td><td>0.5</td><td>Half-sine</td><td>15.4</td></tr><tr><td>Lead</td><td>100</td><td>6</td><td>Half-sine</td><td>12.3</td></tr></table>
Bending		Shall be mounted on a FR4 substrate of the following dimensions: >=0805:40x100x1.2mm <0805:40x100x0.8mm Bending depth: >=0805:1.2mm <0805:0.8mm duration of 10 sec.

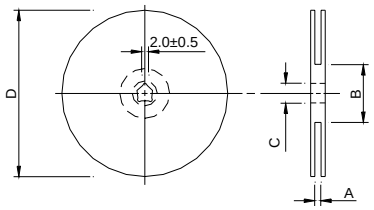
<table>
<tr><th>Item</th><th>Performance</th><th>Test Method and Remarks</th></tr>
<tr><td>Soderability</td><td>More than 95% of the terminal electrode should be covered with solder。</td><td>Preheat: 150℃,60sec.。
Solder: Sn99.5%-Cu0. 5%。
Temperature: 245±5℃。
Flux for lead free: Rosin. 9.5%。
Dip time: 4±1sec。
Depth: completely cover the termination</td></tr>
<tr><td>Resistance to Soldering Heat</td><td rowspan="2">Appearance：No damage.
Inductance：within±10% of initial value
Q：Shall not exceed the specification value.
RDC：within ±15% of initial value and shall not exceed the specification value</td><td>Number of heat cycles: 1
<table><tr><td>Temperature (°C)</td><td>Time(s)</td><td>Temperature ramp/immersion and emersion rate</td></tr><tr><td>260 ±5(solder temp)</td><td>10 ±1</td><td>25mm/s ±6 mm/s</td></tr></table></td></tr>
<tr><td>Terminal Strength</td><td>Preconditioning:Run through IR reflow for 2 times.(IPC/JEDEC J-STD-020DClassification Reflow Profiles
With the component mounted on a PCB with the device to be tested, apply a force (>0805:1kg , <=0805:0.5kg)to the side of a device being tested. This force shall be applied for 60 +1 seconds. Also the force shall be applied gradually as not to apply a shock to the component being tested.
 
</td></tr>
</table>

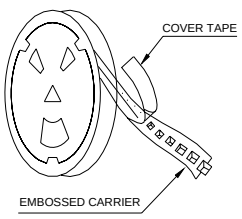
8. Soldering



9. Packaging Information

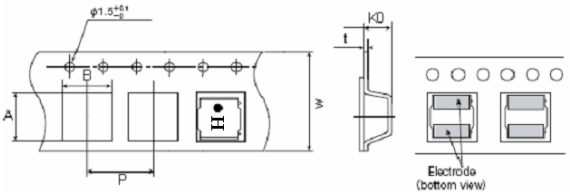
(1) Reel Dimension





Type	A(mm)	B(mm)	C(mm)	D(mm)
HPC4018B	13.5±1.0	80±2.0	13±0.5	330±3.0

(2) Tape Dimension



Type	A(mm)	B(mm)	Ko(mm)	P(mm)	W(mm)	t(mm)
HPC4018B	4.3±0.1	4.3±0.1	2.1±0.1	8.0±0.1	12±0.3	0.3±0.1

(3) Packaging Quantity

Type	Chip / Reel
HPC4018B	3500

Application Notice

・Storage Conditions (component level)
To maintain the solderability of terminal electrodes:
1. TAI-TECH products meet IPC/JEDEC J-STD-020D standard-MSL, level 1.
2. Temperature and humidity conditions: Less than 40℃ and 60% RH.
3. Recommended products should be used within 12 months form the time of delivery.
4. The packaging material should be kept where no chlorine or sulfur exists in the air.

・Transportation
1. Products should be handled with care to avoid damage or contamination from perspiration and skin oils.
2. The use of tweezers or vacuum pick up is strongly recommended for individual components.
3. Bulk handling should ensure that abrasion and mechanical shock are minimized.

測試報告
Test Report

號碼(No.) : CE/2013/C5949 日期(Date) : 2014/01/07 頁數(Page) : 1 of 12

西北臺慶科技股份有限公司 / TAI-TECH ADVANCED ELECTRONICS CO., LTD.
(東莞臺慶精密電子有限公司 / TAI-TECH ADVANCED ELECTRONICS (DONGGUAN) CO. LTD.)
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以下測試樣品係由申請廠商所提供及確認 (The following sample(s) was/were submitted and identified by/on behalf of the applicant as):

樣品名稱(Sample Description)	:	SMD POWER INDUCTOR
樣品型號(Style/Item No.)	:	HPC, MDC, FPC, FWP, SPC, SPI, UHP, DFP, TLPC, TLPH, TLI SERIES
收件日期(Sample Receiving Date)	:	2013/12/30
測試期間(Testing Period)	:	2013/12/30 TO 2014/01/07

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測試結果(Test Results) : 請見下一頁 (Please refer to next pages).

SGS TAIWAN LTD.

Troy Chang / Manager-Tech
Signed for and on behalf of
SGS TAIWAN LTD.
Chemical Laboratory – Taipei

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測試結果(Test Results)

測試部位(PART NAME)No.1 : 整體混測 (MIXED ALL PARTS)

測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測極限值 (MDL)	結果 (Result) No.1
鎘 / Cadmium (Cd)	mg/kg	參考IEC 62321-5: 2013方法，以感應耦合電漿原子發射光譜儀檢測. / With reference to IEC 62321-5: 2013 and performed by ICP-AES.	2	n.d.
鉛 / Lead (Pb)	mg/kg	參考IEC 62321-5: 2013方法，以感應耦合電漿原子發射光譜儀檢測. / With reference to IEC 62321-5: 2013 and performed by ICP-AES.	2	n.d.
汞 / Mercury (Hg)	mg/kg	參考IEC 62321-4: 2013方法，以感應耦合電漿原子發射光譜儀檢測. / With reference to IEC 62321-4: 2013 and performed by ICP-AES.	2	n.d.
六價鉻 / Hexavalent Chromium Cr(VI)	mg/kg	參考IEC 62321: 2008方法，以UV-VIS檢測. / With reference to IEC 62321: 2008 and performed by UV-VIS.	2	n.d.

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測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測極限值 (MDL)	結果 (Result) No.1
鄰苯二甲酸甲苯基丁酯 / BBP (Benzyl butyl phthalate) (CAS No.: 85-68-7)	%	參考EN 14372, 以氣相層析/質譜儀檢測之. / With reference to EN 14372. Analysis was performed by GC/MS.	0.003	n.d.
鄰苯二甲酸二 (2-乙基己基)酯 / DEHP (Di- (2-ethylhexyl) phthalate) (CAS No.: 117-81-7)	%	參考EN 14372, 以氣相層析/質譜儀檢測之. / With reference to EN 14372. Analysis was performed by GC/MS.	0.003	n.d.
鄰苯二甲酸二異癸酯 / DIDP (Di-isodecyl phthalate) (CAS No.: 26761-40-0; 68515-49-1)	%	參考EN 14372, 以氣相層析/質譜儀檢測之. / With reference to EN 14372. Analysis was performed by GC/MS.	0.01	n.d.
鄰苯二甲酸二異壬酯 / DINP (Di-isononyl phthalate) (CAS No.: 28553-12-0; 68515-48-0)	%	參考EN 14372, 以氣相層析/質譜儀檢測之. / With reference to EN 14372. Analysis was performed by GC/MS.	0.01	n.d.
鄰苯二甲酸二正辛酯 / DNOP (Di-n-octyl phthalate) (CAS No.: 117-84-0)	%	參考EN 14372, 以氣相層析/質譜儀檢測之. / With reference to EN 14372. Analysis was performed by GC/MS.	0.003	n.d.
鄰苯二甲酸二丁酯 / DBP (Dibutyl phthalate) (CAS No.: 84-74-2)	%	參考EN 14372, 以氣相層析/質譜儀檢測之. / With reference to EN 14372. Analysis was performed by GC/MS.	0.003	n.d.
鄰苯二甲酸二異丁酯 / DIBP (Di-isobutyl phthalate) (CAS No.: 84-69-5)	%	參考EN 14372, 以氣相層析/質譜儀檢測之. / With reference to EN 14372. Analysis was performed by GC/MS.	0.003	n.d.

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測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測極限值 (MDL)	結果 (Result) No.1
六溴環十二烷及所有主要被辨別出的異構物 / Hexabromocyclododecane (HBCDD) and all major diastereoisomers identified (α- HBCDD, β- HBCDD, γ- HBCDD) (CAS No.: 25637-99-4 and 3194-55-6 (134237-51-7, 134237-50-6, 134237-52-8))	mg/kg	參考IEC 62321: 2008方法, 以氣相層析/質譜儀檢測. / With reference to IEC 62321: 2008 method. Analysis was performed by GC/MS.	5	n.d.
多溴聯苯總和 / Sum of PBBs	mg/kg	參考IEC 62321: 2008方法, 以氣相層析/質譜儀檢測. / With reference to IEC 62321: 2008 and performed by GC/MS.	-	n.d.
一溴聯苯 / Monobromobiphenyl	mg/kg		5	n.d.
二溴聯苯 / Dibromobiphenyl	mg/kg		5	n.d.
三溴聯苯 / Tribromobiphenyl	mg/kg		5	n.d.
四溴聯苯 / Tetrabromobiphenyl	mg/kg		5	n.d.
五溴聯苯 / Pentabromobiphenyl	mg/kg		5	n.d.
六溴聯苯 / Hexabromobiphenyl	mg/kg		5	n.d.
七溴聯苯 / Heptabromobiphenyl	mg/kg		5	n.d.
八溴聯苯 / Octabromobiphenyl	mg/kg		5	n.d.
九溴聯苯 / Nonabromobiphenyl	mg/kg		5	n.d.
十溴聯苯 / Decabromobiphenyl	mg/kg		5	n.d.

測試報告
Test Report

西北臺慶科技股份有限公司 / TAI-TECH ADVANCED ELECTRONICS CO., LTD.
(東莞臺慶精密電子有限公司 / TAI-TECH ADVANCED ELECTRONICS (DONGGUAN) CO. LTD.)
(臺慶精密電子(昆山)有限公司 / TAI-TECH ADVANCED ELECTRONICS (KUN-SHAN) CO. LTD.)
(耀鑽科技股份有限公司 / YOSONIC TECHNOLOGY CO., LTD.)
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(廣東省東莞市黃江鎮黃牛埔福祥街2號 / NO. 2, FUXIANG STREET, HUANGNIUPU, HUANGJIANG TOWN, DONGGUAN, GUANGDONG)
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測試項目 (Test Items)	單位 (Unit)	測試方法 (Method)	方法偵測極限值 (MDL)	結果 (Result) No.1
多溴聯苯醚總和 / Sum of PBDEs	mg/kg	參考IEC 62321: 2008方法，以氣相層析/質譜儀檢測. / With reference to IEC 62321: 2008 and performed by GC/MS.	-	n.d.
一溴聯苯醚 / Monobromodiphenyl ether	mg/kg		5	n.d.
二溴聯苯醚 / Dibromodiphenyl ether	mg/kg		5	n.d.
三溴聯苯醚 / Tribromodiphenyl ether	mg/kg		5	n.d.
四溴聯苯醚 / Tetrabromodiphenyl ether	mg/kg		5	n.d.
五溴聯苯醚 / Pentabromodiphenyl ether	mg/kg		5	n.d.
六溴聯苯醚 / Hexabromodiphenyl ether	mg/kg		5	n.d.
七溴聯苯醚 / Heptabromodiphenyl ether	mg/kg		5	n.d.
八溴聯苯醚 / Octabromodiphenyl ether	mg/kg		5	n.d.
九溴聯苯醚 / Nonabromodiphenyl ether	mg/kg		5	n.d.
十溴聯苯醚 / Decabromodiphenyl ether	mg/kg		5	n.d.
鹵素 / Halogen				
鹵素 (氟) / Halogen-Fluorine (F) (CAS No.: 14762-94-8)	mg/kg	參考BS EN 14582:2007，以離子層析儀分析. / With reference to BS EN 14582:2007. Analysis was performed by IC.	50	n.d.
鹵素 (氯) / Halogen-Chlorine (Cl) (CAS No.: 22537-15-1)	mg/kg		50	n.d.
鹵素 (溴) / Halogen-Bromine (Br) (CAS No.: 10097-32-2)	mg/kg		50	n.d.
鹵素 (碘) / Halogen-Iodine (I) (CAS No.: 14362-44-8)	mg/kg		50	n.d.

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備註(Note)：

1. mg/kg = ppm；0.1wt% = 1000ppm
2. n.d. = Not Detected (未檢出)
3. MDL = Method Detection Limit (方法偵測極限值)
4. "-" = Not Regulated (無規格值)
5. 樣品的測試是基於申請人要求混合測試，報告中的混合測試結果不代表其中個別單一材質的含量. (The samples was/were analyzed on behalf of the applicant as mixing sample in one testing. The above results was/were only given as the informality value.)

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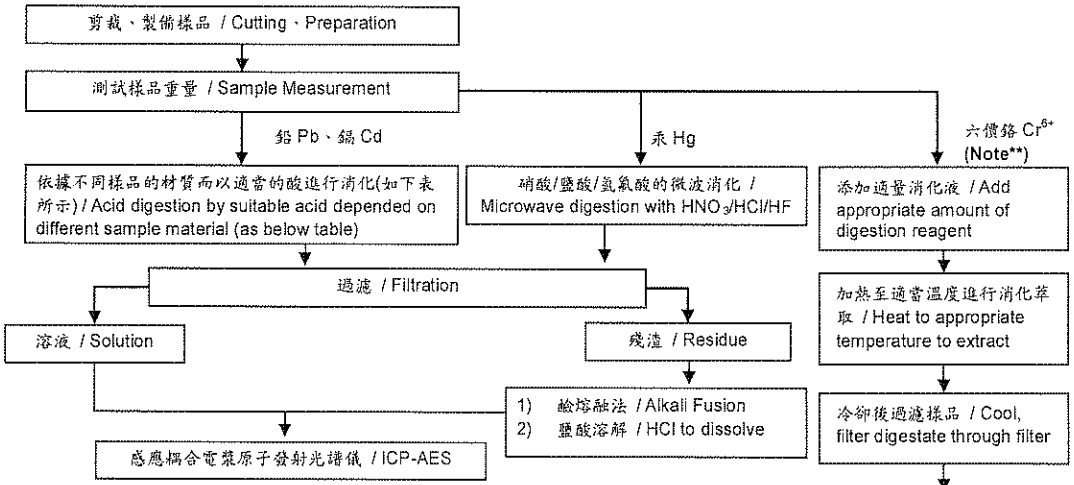
1) 根據以下的流程圖之條件，樣品已完全溶解。(六價鉻測試方法除外) / These samples were dissolved totally by pre-conditioning method according to below flow chart. (Cr^{6+} test method excluded)
2) 測試人員：楊登偉 / Name of the person who made measurement: Climbgreat Yang
3) 測試負責人：張啓興 / Name of the person in charge of measurement: Troy Chang



樣品材質 / Sample Material	消化酸液種類 / Digestion Acid
鋼, 銅, 鋁, 焊錫 / Steel, copper, aluminum, solder	王水, 硝酸, 鹽酸, 氫氟酸, 雙氧水 / Aqua regia, HNO_3, HCl, HF, H_2O_2
玻璃 / Glass	硝酸,氫氟酸 / HNO_3/HF
金, 鉑, 鈀, 陶瓷 / Gold, platinum, palladium, ceramic	王水 / Aqua regia
銀 / Silver	硝酸 / HNO_3
塑膠 / Plastic	硫酸, 雙氧水, 硝酸, 鹽酸 / H_2SO_4, H_2O_2, HNO_3, HCl
其他 / Others	加入適當的試劑至完全溶解 / Added appropriate reagent to total digestion

Note (For IEC 62321)**
(1) 針對非金屬材料加入鹼性消化液，加熱至 90~95℃ 萃取. / For non-metallic material, add alkaline digestion reagent and heat to 90~95 ℃.
(2) 針對金屬材料加入純水，加熱至沸騰萃取. / For metallic material, add pure water and heat to boiling.

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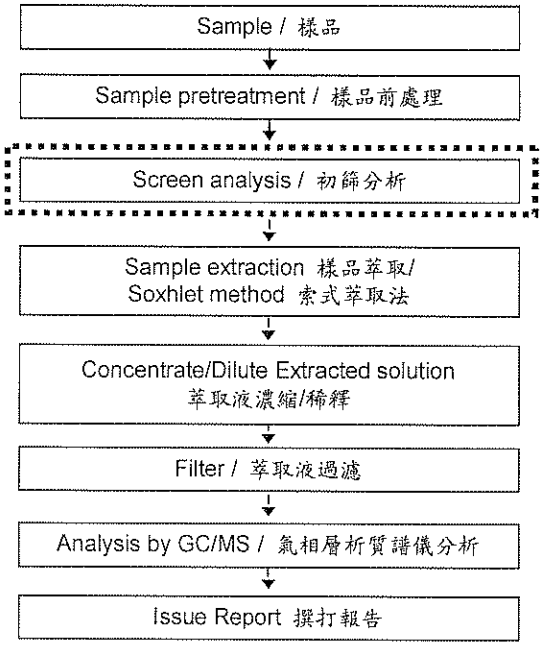
多溴聯苯/多溴聯苯醚分析流程圖 / PBB/PBDE analytical FLOW CHART

- 測試人員：翁賜彬 / Name of the person who made measurement: Roman Wong
- 測試負責人：張啓興 / Name of the person in charge of measurement: Troy Chang

初次測試程序 / First testing process ——→
選擇性篩檢程序 / Optional screen process ▪▪▪▪▪▪▪▪
確認程序 / Confirmation process — · — ·▸



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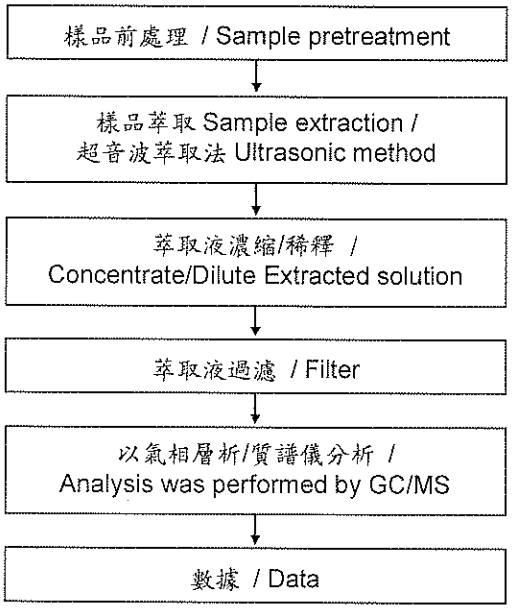
六溴環十二烷分析流程圖 / HBCDD analytical flow chart

- 測試人員：翁賜彬 / Name of the person who made measurement: Roman Wong
- 測試負責人：張啓興 / Name of the person in charge of measurement: Troy Chang



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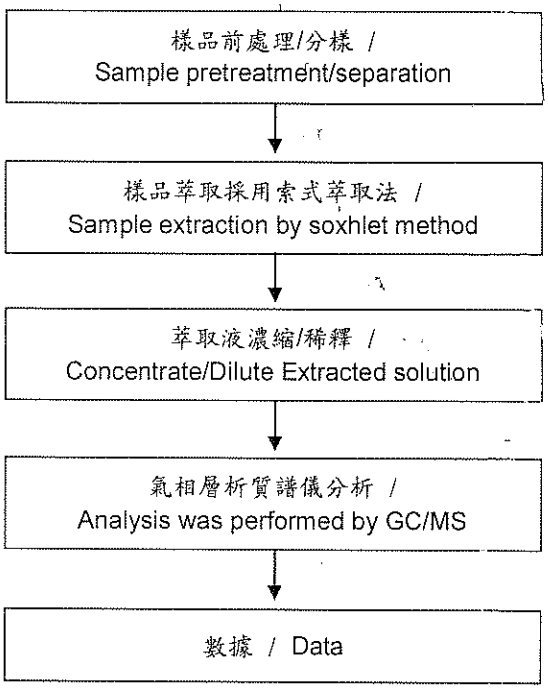
可塑劑分析流程圖 / Analytical flow chart of phthalate content

- 測試人員：翁賜彬 / Name of the person who made measurement: Roman Wong
- 測試負責人：張啓興 / Name of the person in charge of measurement: Troy Chang



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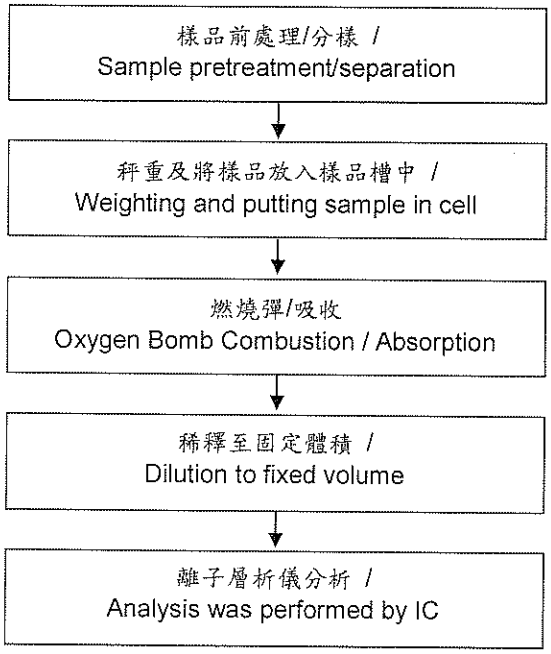
鹵素分析流程圖 / Analytical flow chart of halogen content

- 測試人員：陳恩臻 / Name of the person who made measurement: Rita Chen
- 測試負責人：張啓興 / Name of the person in charge of measurement: Troy Chang



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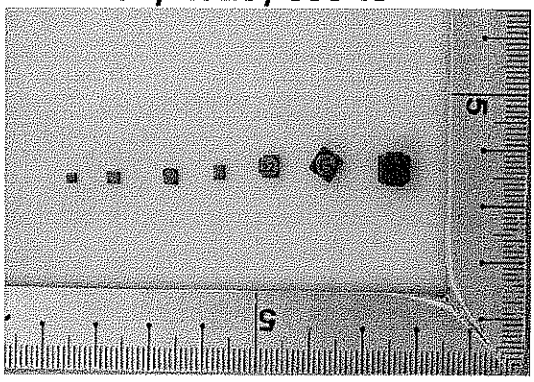
* 照片中如有箭頭標示，則表示爲實際檢測之樣品/部位. *
(The tested sample / part is marked by an arrow if it's shown on the photo.)

CE/2013/C5949



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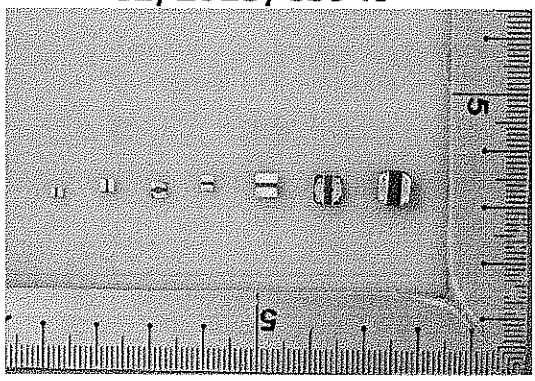

** 報告結尾 (End of Report) **